

L9013RLT1G S-L9013RLT1G

General Purpose Transistors NPN Silicon

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L9013RLT1G	13R	3000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

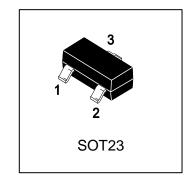
Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	VCEO	25	V
Collector-Base voltage	VCBO	40	V
Emitter-Base Voltage	VEBO	5	V
Collector current-continuoun	IC	500	mA

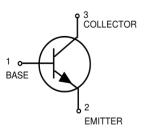
4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation,	PD		
FR-5 Board (Note 1) @ TA = 25°C		225	mW
Derate above 25°C		1.8	mW/℃
Thermal Resistance, Junction-to-Ambient	RØJA	556	°C/W
Total Device Dissipation,	PD		
Alumina Substrate, (Note 2)@ TA = 25°C		300	mW
Derate above 25°C		2.4	mW/℃
Thermal Resistance, Junction-to-Ambient	RØJA	417	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

1. FR–5 = 1.0×0.75×0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.







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5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Тур.	Max.	Unit		
Collector-Emitter Breakdown Voltage	V(BR)CEO	25	-	-	V		
(IC =1.0mA)	V(BIX)CLO				v		
Emitter-Base Breakdown Voltage	V(BR)EBO	5	-	-	V		
(IE = 100µA)	V(BI()EBO				v		
Collector-Base Breakdown voltage	V(BR)CBO	40			V		
(IC = 100µA)	V(BR)CBC	40	-	-	v		
Collector Cutoff Current	ICBO	_	_	150	nA		
(VCB = 35 V)	1000	-	-	150			
Emitter Cutoff Current	IEBO	_	_	150	nA		
(VEB = 4V)	ILDO	-	-	150			
ON CHARACTERISTICS	ON CHARACTERISTICS						
DC Current Gain	HFE	200		400			
(IC =50mA, VCE =1V)		200	-	400			
Collector-Emitter Saturation Voltage	VCE(S)		-	0.6	V		
(IC =500mA,IB =50mA)	VOL(0)	-			v		



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6.OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

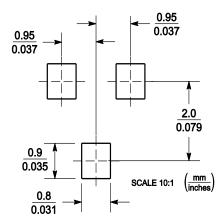
2. CONTROLLING DIMENSION: MILLIMETERS.

3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

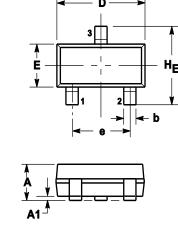
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

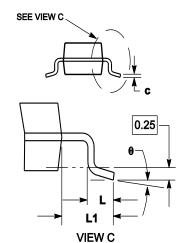
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1	1.11	0.035	0.04	0.044	
A1	0.01	0.06	0.1	0.001	0.002	0.004	
b	0.37	0.44	0.5	0.015	0.018	0.02	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.9	3.04	0.11	0.114	0.12	
Е	1.20	1.3	1.4	0.047	0.051	0.055	
е	1.78	1.9	2.04	0.07	0.075	0.081	
L	0.10	0.2	0.3	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
H _E	2.10	2.4	2.64	0.083	0.094	0.104	
θ	0°		10°	0°		10°	

7.SOLDERING FOOTPRINT











DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
- Before you use our Products for new Project, you are requested to carefully read this document and fully under--stand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价,库存,交付和生命周期等信息

>>LRC(乐山无线电)